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MGFC40V3742

Unit: millimeters (inches)

3.7 ~ 4.2GHz BAND 10W INTERNALLY MATCHED GaAs FET

OUTLINE DRAWING

DESCRIPTION

The MGFC40V3742 is an internally impedance-matched GaAs power FET especially designed for use in 3.7 ~ 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 10W (TYP.) @ f= $3.7 \sim 4.2$ GHz High power gain GLP = 11 dB (TYP.) @ f= $3.7 \sim 4.2$ GHz High power added efficiency P.A.E. = 32 % (TYP.) @ f= $3.7 \sim 4.2$ GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @Po=29(dBm) S.C.L.

APPLICATION

item 01 : 3.7~4.2 GHz band power amplifier item 51 : 3.7~4.2 GHz band digital radio communication

QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

VDS = 10(V)ID = 2.4 (A) Rg = 50(ohm) Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	-15	V	
VGSO	Gate to source voltage	-15	V	
ID	Drain current	7.5	Α	
IGR	Reverse gate current	-20	mA	
IGF	Forward gate current	42 m/		
PT	Total power dissipation *1	42.8	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	

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*1 : Tc=25 deg.C

ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
Symbol	Falameter	Test conditions	Min.	Тур.	Max.	Unit
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	4.5	6	Α
gm	Transconductance	VDS=3V, ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=40mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression		39.5	40.5	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=2.4A, f=3.7~4.2GHz	9	11	-	dB
ID	Drain current		-	2.4	-	Α
P.A.E.	Power added efficiency		-	32	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	-	3.5	deg.C/W

*1 : item -51, 2 tone test, Po=29dBm Single Carrier Level, f=4.2GHz, Delta f=10MHz

*2 : Channel to case



24+/-0.3 R1.25 (1)0.6+/-0.15 2MIN R1.2 17.4+/-0.3 8.0+/-0.2 5.8 (2) MIN (3) 20.4 + / - 0.213 4 0.0 -(1): GATE (2): SOURCE (FLANGE (3): DRAIN **GF-18**

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MITSUBISHI SEMICONDUCTOR <GaAs FET>

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3.7 ~ 4.2GHz BAND 10W INTERNALLY MATCHED GaAs FET

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